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CERTIFICATE OF TRANSMISSION**January 10, 2003**

Atty Docket No. :	JCLA4827-CIP
Appl. No. :	10/055,157
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BY FACSIMILE ONLY

Fax No. : 703-872-9318
Attention : Examiner MAI, ANH D.
Group Unit : 2814
From : Jiawei Huang, Reg. No. 43,330
MESSAGE : Enclosed herewith are:
[x] Transmittal sheet.
[x] Amendment in 16 pages.
[x] Amended drawings of Figs. 1B, 1C, and 1D with clean copy thereof.

FAX RECEIVED**JAN 10 2003****TECHNOLOGY CENTER 2800**

Sir:

I hereby certify that this correspondence is being facsimile transmitted to the Patent and Trademark Office on January 10, 2003 at the above indicated fax number.

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Atty Docket No.: JCLA4827-CIP

Serial No.: 10/055,157

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of :

Bih-Tiao Lin

Examiner : Mai, Anh D.

Serial No.: 10/055,157

Art Unit : 2814

Filed : October 22, 2001

Docket No.: JCLA4827-CIP

For : FABRICATION METHOD OF
SHALLOW TRENCH ISOLATION**AMENDMENT AND RESPONSE TO OFFICE ACTION****FAX RECEIVED**Assistant Commissioner of Patents and Trademarks
Washington, DC 20231

JAN 10 2003

Sir:

TECHNOLOGY CENTER 2800

The Office Action mailed September 10, 2002 (Paper No. 7), has been carefully considered. In response thereto, please enter the following amendment and consider the following remarks.

In The Specification:

Please replace the paragraph beginning at page 2, lines 22, with the following rewritten

paragraph:

--The formation method of the insulating layer mentioned above is, for example, high density plasma chemical vapor deposition (HDPCVD). The high density plasma of HDPCVD has a bombarding effect; therefore the insulating layer has substantially vertical sidewalls above the edge of the active areas. The screen layer is formed by, for example, floatable precursors.